

Roll No.:

National Institute of Technology, Delhi

Name of the Examination: B. Tech

Branch : EEE

Semester : III

Title of the Course : Analog Electronics

Course Code : ECB 206

Time: 2 Hours

Maximum Marks: 25

Note :

Section A

Attempt any two

$4 \times 2 = 8$

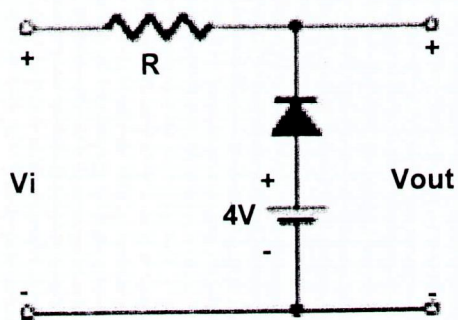
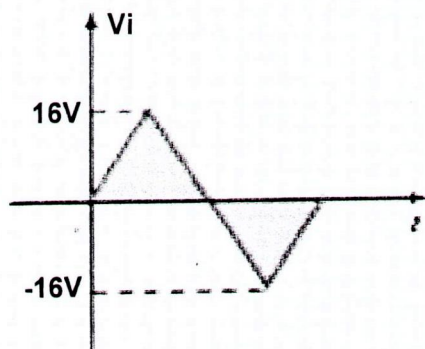
- 1) Discuss half wave and full wave voltage doubler circuit?
- 2) Explain construction and working of common emitter NPN transistor configuration?
- 3) Discuss full wave bridge rectifier?

Section B

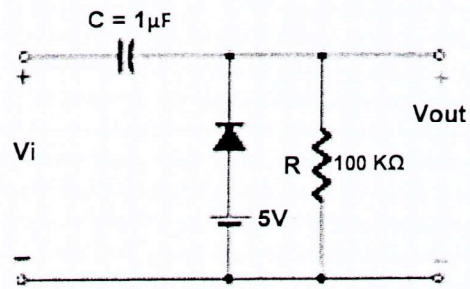
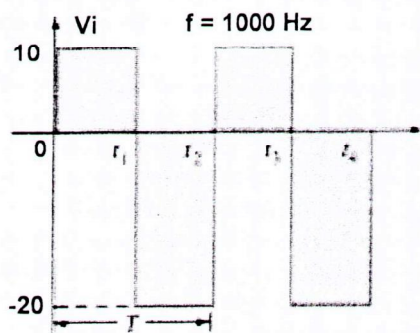
Attempt any two

$4 \times 2 = 8$

- 4) A transistor operating in CB configuration of $I_c = 2.98$ mA, $I_E = 3$ mA, and $I_{co} = 0.01$ mA. What current will flow in the collector circuit of this transistor when connected in CE configuration with a base current of $30 \mu\text{A}$?
- 5) Determine V_{out} for the network?



6) Determine V_{out} for the network?



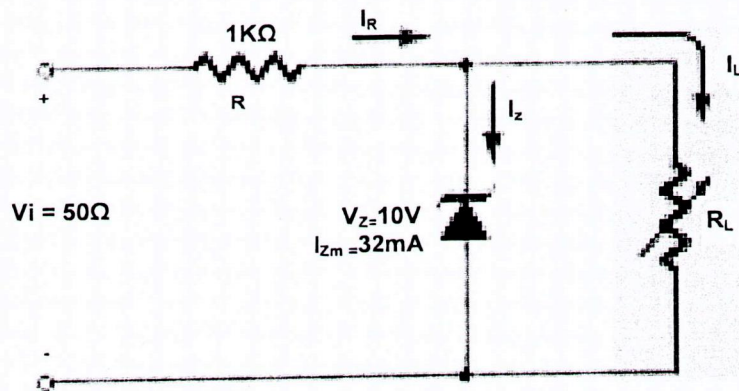
7) Explain the working of PN junction with its I-V characteristics.

Section c

Attempt any three

3 × 3 = 9

- 8) The reverse leakage current of the transistor when connected in CB configuration is $0.2 \mu A$ and it is $18 \mu A$ when the same transistor is connected in CE configuration. Calculate α and β of the transistor?
- 9) Derive the relationship among α , β and γ ? The transistor has $I_E = 10 \text{ mA}$ and $\alpha = 0.98$. Determine the value of I_C and I_B ?
- 10) (a) For the network as shown in figure, determine the range of R_L and I_L that will result in V_{R_L} being maintained at 10V.
(b) Determine the maximum wattage rating of the diode.



11) A 10V regulated dc power supply has a regulation of 0.002. Find the magnitude of variation in o/p volt.